PQMD16

NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = 47 kΩ

15 December 2015 **Product data sheet**

1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

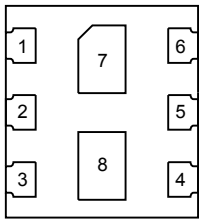
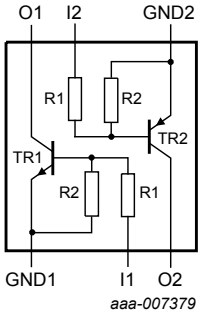
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
V_{CEO}	collector-emitter voltage	open base		-	-	50	V
I_O	output current			-	-	100	mA
Per transistor; for the PNP transistor with negative polarity							
R1	bias resistor 1	T_{amb} = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	1.7	2.13	2.6	

[1] See section "Test information" for resistor calculation and test conditions.

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	 Transparent top view **DFN1010B-6 (SOT1216)**	
2	I1	input (base) TR1		
3	O2	output (collector) TR2		
4	GND2	GND (emitter) TR2		
5	I2	input (base) TR2		
6	O1	output (collector) TR1		
7	O1	output (collector) TR1		
8	O2	output (collector) TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PQMD16	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
PQMD16	B 100

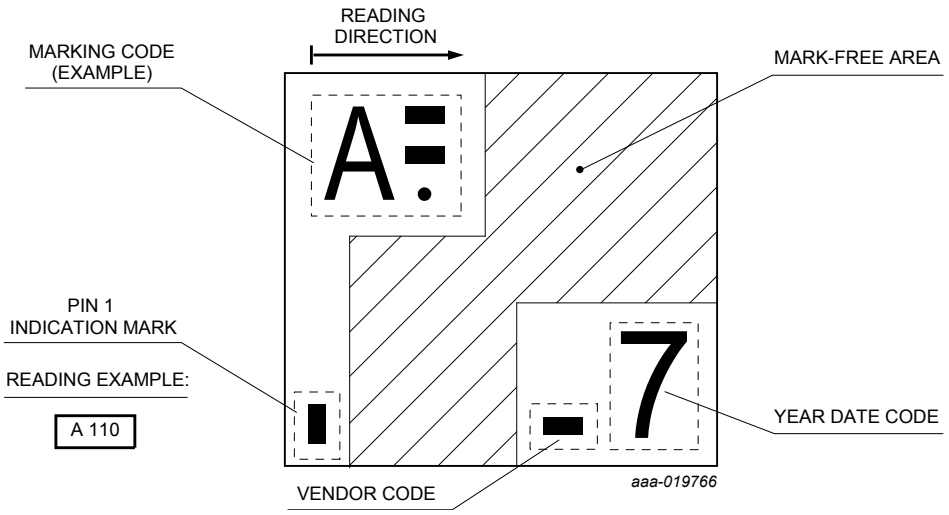


Fig. 1. DFN1010B-6 (SOT1216) binary marking code description

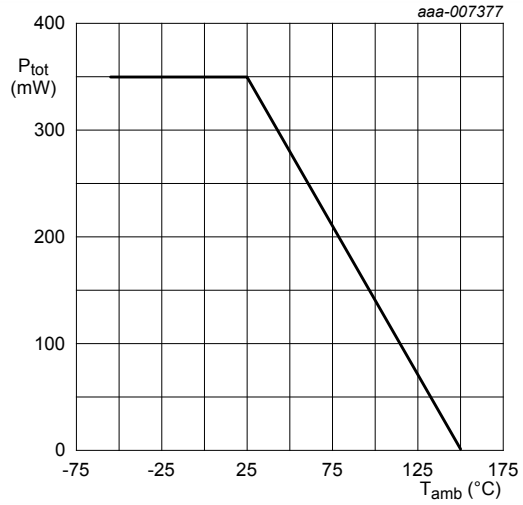
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
V_I	input voltage	TR1; positive		-	40	V
		TR1; negative		-	-7	V
		TR2; positive		-	7	V
		TR2; negative		-	-40	V
I_O	output current			-	100	mA
I_{CM}	peak collector current	$t_p \leq 1$ ms; single pulse		-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	230	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	350	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

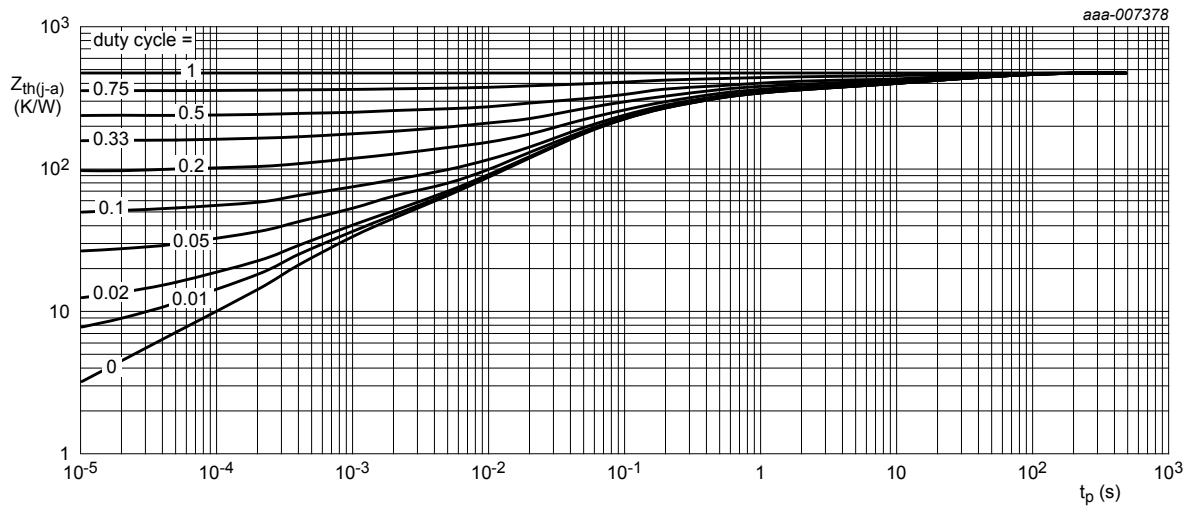
Fig. 2. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

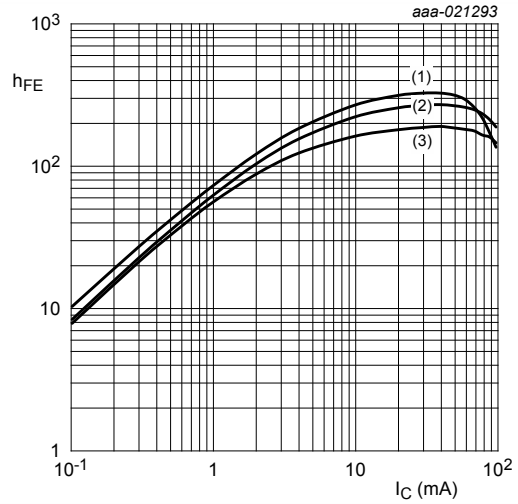
Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity							
I_{CBO}	collector-base cut-off current (emitter open)	V_{CB} = 50 V; I_E = 0 A; T_{amb} = 25 °C		-	-	100	nA
I_{CEO}	collector-emitter cut-off current (base open)	V_{CE} = 30 V; I_B = 0 A; T_{amb} = 25 °C		-	-	1	µA
		V_{CE} = 30 V; I_B = 0 A; T_j = 150 °C		-	-	50	µA
I_{EBO}	emitter-base cut-off current (collector open)	V_{EB} = 5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	120	µA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 5 mA; T_{amb} = 25 °C		80	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_C = 100 µA; T_{amb} = 25 °C		-	0.8	0.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_C = 2 mA; T_{amb} = 25 °C		2	1.1	-	V
R1	bias resistor 1	T_{amb} = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	1.7	2.13	2.6	
C_C	collector capacitance	V_{CB} = 10 V; I_E = 0 A; f = 1 MHz; T_{amb} = 25 °C; TR1 (NPN)		-	-	2.5	pF
		V_{CB} = -10 V; I_E = 0 A; f = 1 MHz; T_{amb} = 25 °C; TR2 (PNP)		-	-	3	pF
f_T	transition frequency	V_{CE} = 5 V; I_C = 10 mA; f = 100 MHz; T_{amb} = 25 °C; TR1 (NPN)	[2]	-	230	-	MHz
		V_{CE} = -5 V; I_C = -10 mA; f = 100 MHz; T_{amb} = 25 °C; TR2 (PNP)	[2]	-	180	-	MHz

[1] See section "Test information" for resistor calculation and test conditions.
[2] Characteristics of built-in transistor



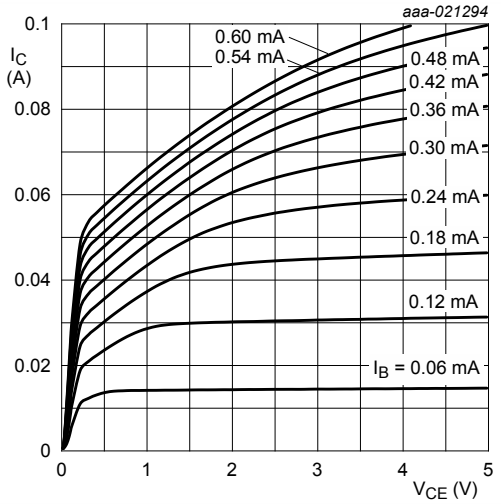
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

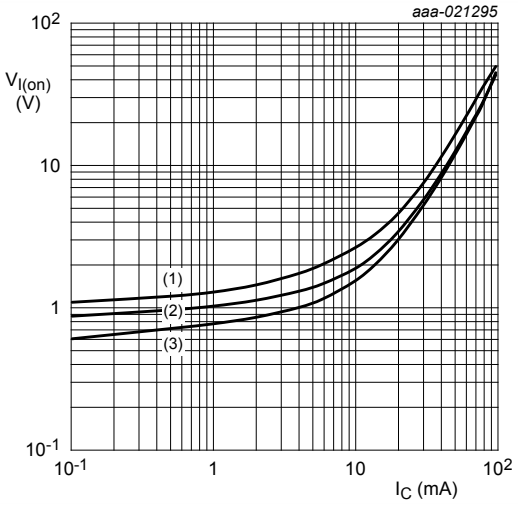
(3) T_{amb} = -40 °C

Fig. 4. NPN transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



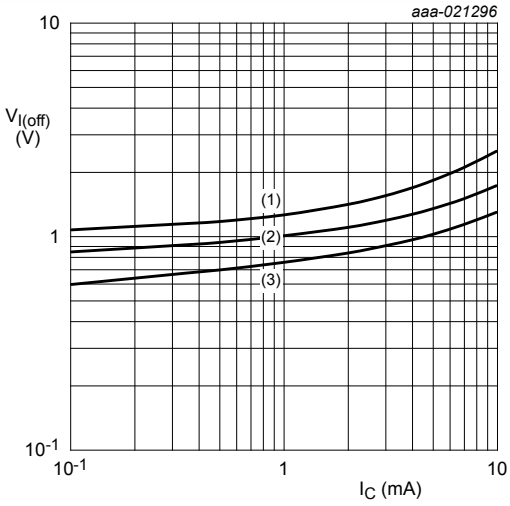
V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



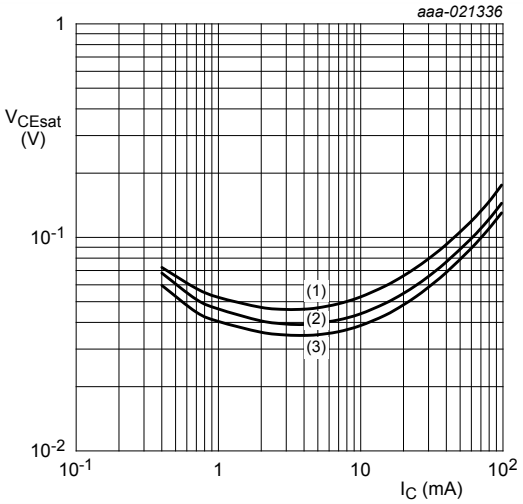
V_{CE} = 5 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



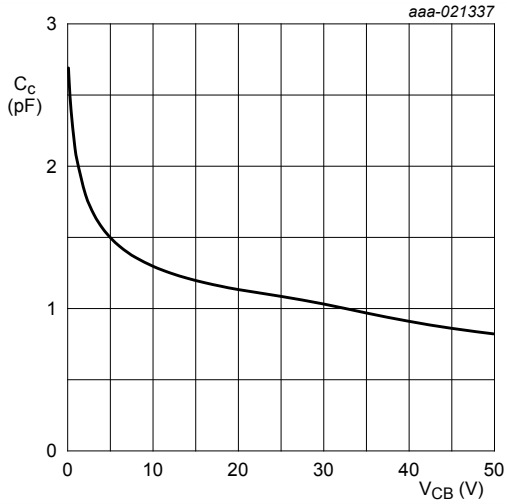
I_C/I_B = 10

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

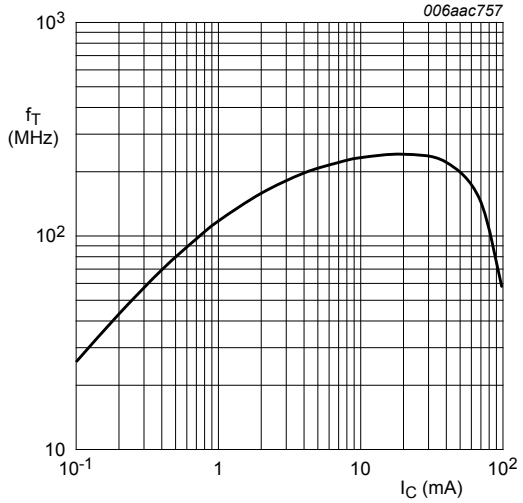
(3) T_{amb} = -40 °C

Fig. 8. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



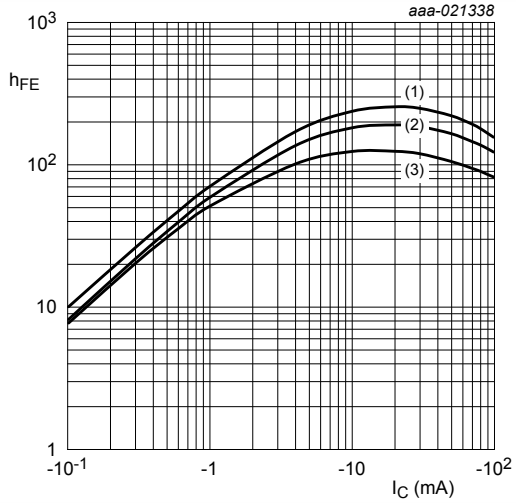
f = 1 MHz; T_{amb} = 25 °C

Fig. 9. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 10. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



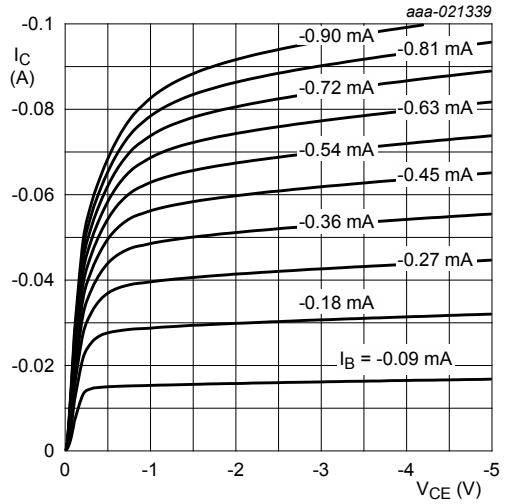
V_{CE} = -5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

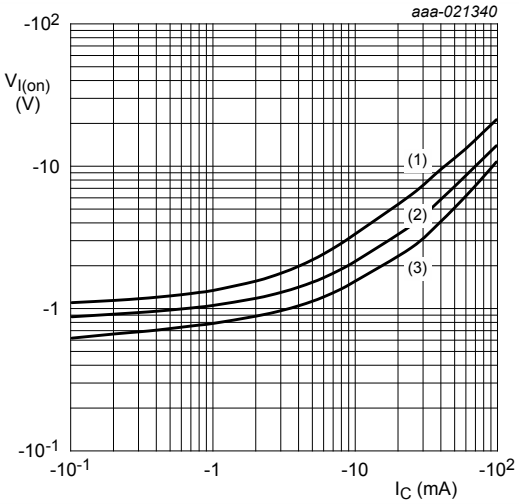
(3) T_{amb} = -40 °C

Fig. 11. PNP transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 12. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



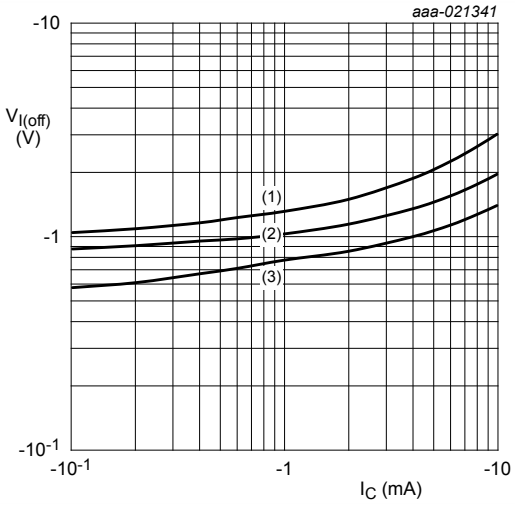
V_{CE} = -0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



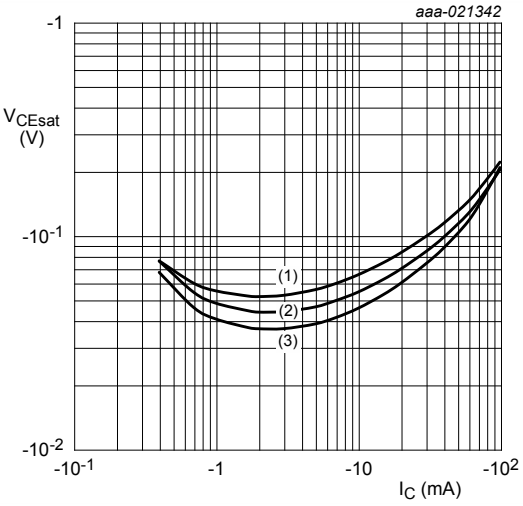
V_{CE} = -5 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



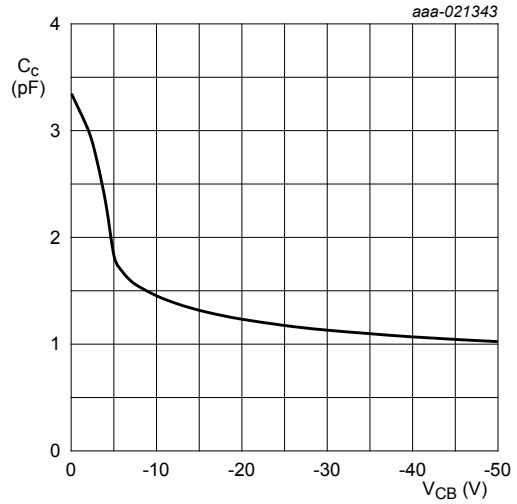
I_C/I_B = 10

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

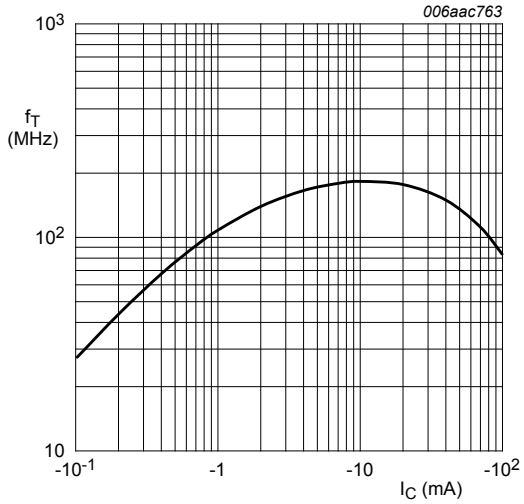
(3) T_{amb} = -40 °C

Fig. 15. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig. 16. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = -5 V; T_{amb} = 25 °C

Fig. 17. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

11.2 Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I_{I2}) - V(I_{I1})}{I_{I2} - I_{I1}}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I_{I4}) - V(I_{I3})}{R1 \cdot (I_{I4} - I_{I3})} - 1$$

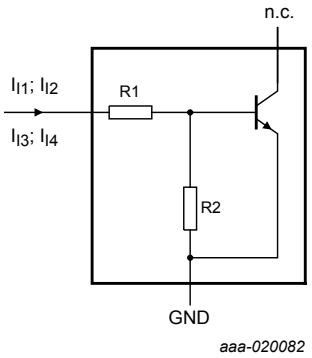


Fig. 18. NPN transistor: Resistor test circuit

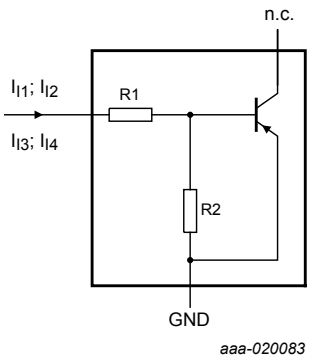


Fig. 19. PNP transistor: Resistor test circuit

11.3 Resistor test conditions

Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I_{I1}	I_{I2}	I_{I3}	I_{I4}
22	47	90 µA	140 µA	-55 µA	-105 µA

12. Package outline

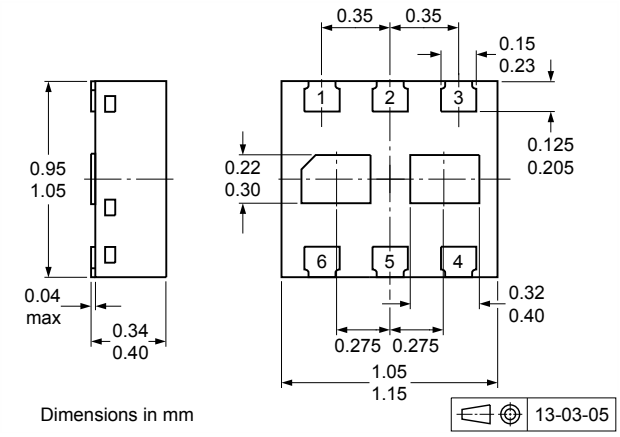


Fig. 20. Package outline DFN1010B-6 (SOT1216)

13. Soldering

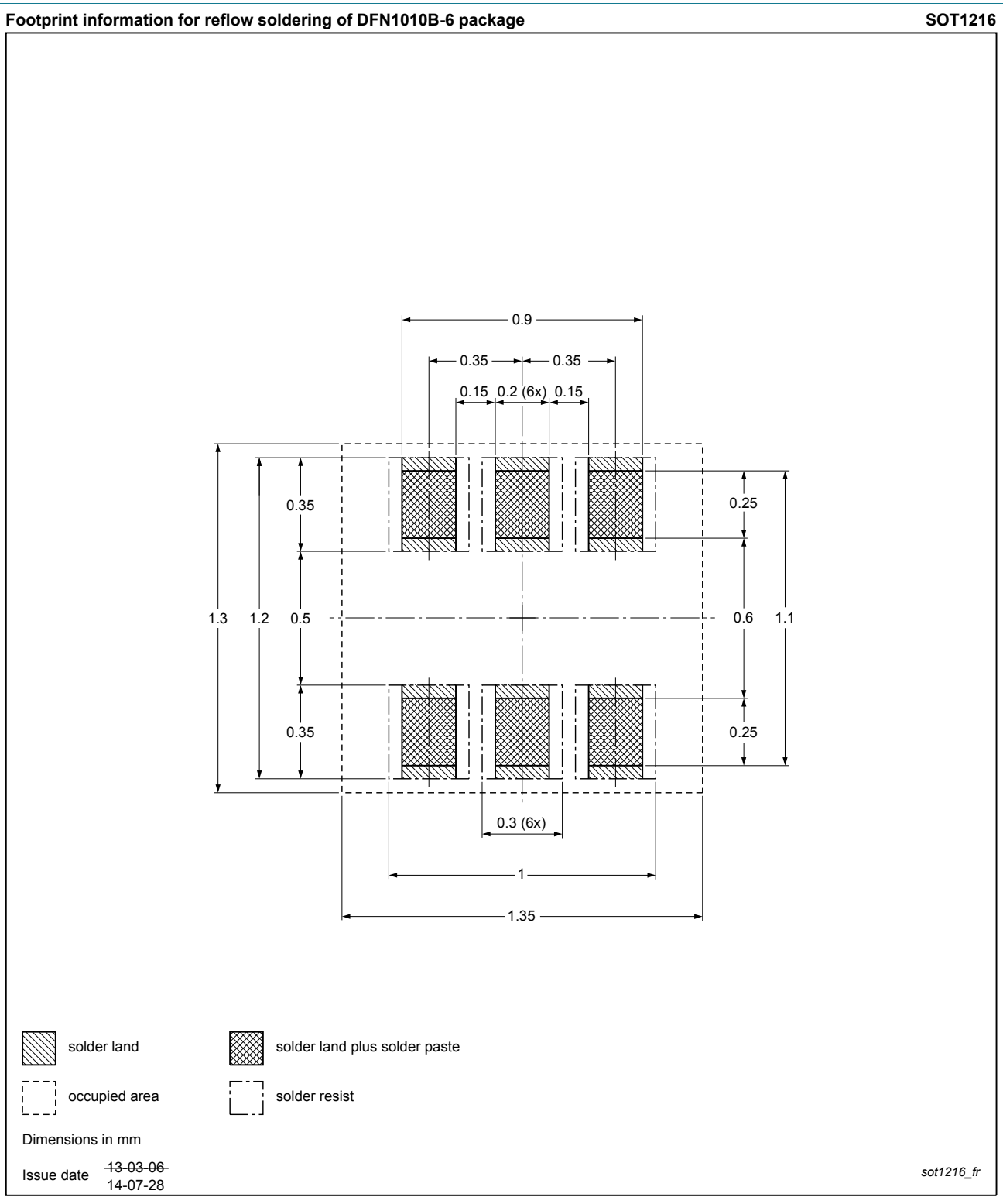


Fig. 21. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMD16 v.1	20151215	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
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